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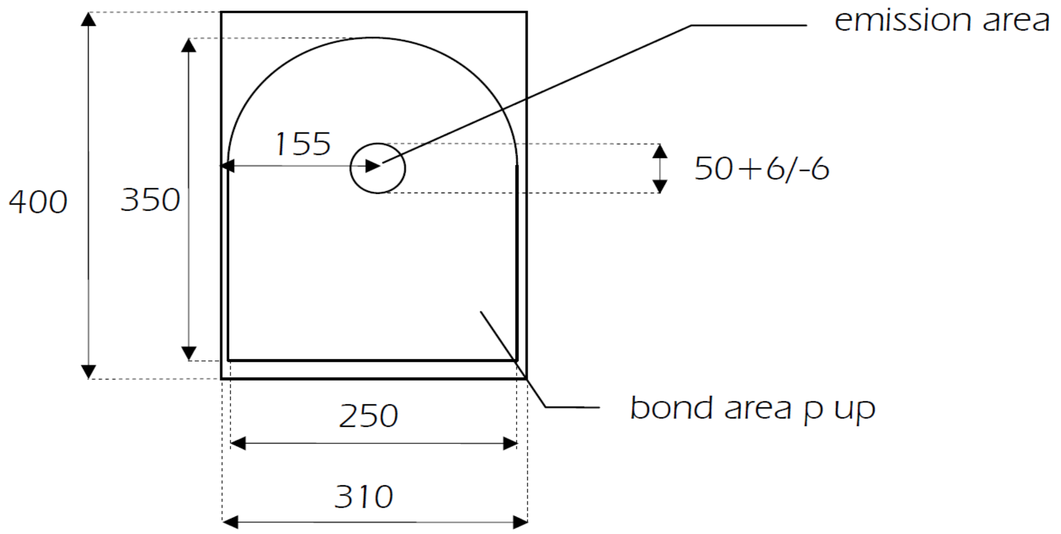
LED Chip Infrared EOLC-850-19-20

Rev. 02, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/GaAs	P (anode) up



Dimensions:

All dimensions in µm

- Chip size: 310 x 400 T16µm ±20 µm
- Thickness: typ. 260±30 µm

Electrodes / Metallization:

- p-side (anode): Au alloy
- n-side (cathode) Au alloy

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=50 mA	V_F		1.95	2.2	V
Reverse current	V_R=5 V	I_R			100	µA
Radiant power*	I_F=20 mA	Φ_e		0.6		mW
Radiant power*	I_F=50 mA	Φ_e	1.0	1.2		mW
Peak wavelength	I_F=50 mA	λ_p		850		nm
Switching times	I_F=20 mA	t_r, t_f		10; 15		ns

*Measured on bare chip on TO-18 header

Art. No. 114 015

RoHS COMPLIANT

Pb Pb-Free